PNP Epitaxial Silicon Transistor

KSA916

Features

- Audio Power Amplifier
- Driver Stage Amplifier
- Complement to KSC2316

ABSOLUTE MAXIMUM RATINGS

(Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-120	V
V _{CEO}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ι _C	Collector Current	-800	mA
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.) (Note 1)

Symbol	Parameter	Value	Unit
PD	Power Dissipation, by $R_{\theta JA}$	900	mW
	Power Dissipation, by $R_{\theta JC}$	3	W
	Derate Above 25°C, by $R_{\theta JA}$	7.2	mW/°C
	Derate Above 25°C, by $R_{\theta JC}$	24	mW/°C
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	130	°C/W
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case	41	°C/W

1. PCB size: FR-4, 76 mm \times 114 mm \times 1.57 mm (3.0 inch \times 4.5 inch \times 0.062 inch) with minimum land pattern size.



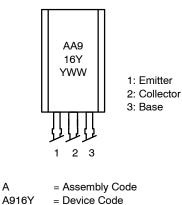
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TO-92 3 LF CASE 135AM

MARKING DIAGRAM



YWW = Date Code

ORDERING INFORMATION

Device	Package	Shipping
KSA916YTA	TO–92 3 LF (Pb–Free)	2000 / Fan-Fold

Downloaded from Arrow.com.

ELECTRICAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = -1 {\rm mA}, I_{\rm E} = 0$	-120	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = -10 mA, I _B = 0	-120	-	-	V
BV_{EBO}	Emitter-Base Breakdown Voltage	I _E = -1 mA, I _C = 0	-5	-	-	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = -120 \text{ V}, \text{ I}_{E} = 0$	-	-	-0.1	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -10 \text{ mA}$	60	-	-	
h _{FE2}	DC Current Gain	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -100 \text{ mA}$	80	-	240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -500 mA, I _B = -50 mA	-	-	-1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -100 \text{ mA}$	-	120	-	MHz
C _{ob}	Output Capacitance	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	-	-	40	pF

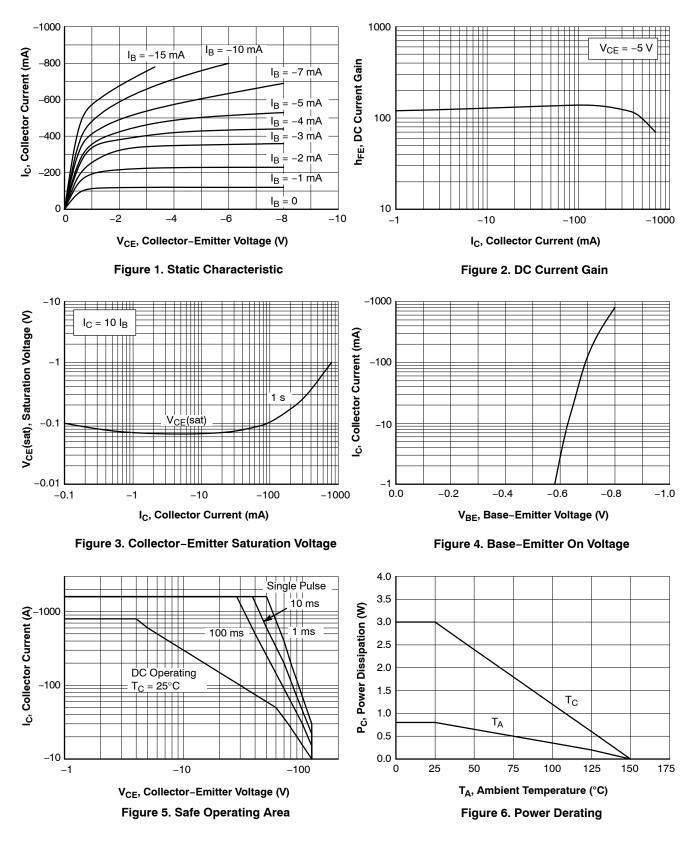
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} CLASSIFICATION

Classification	0	Y
h _{FE2}	80 ~ 160	120 ~ 240

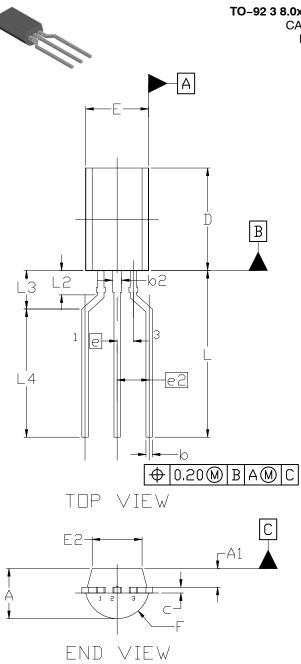
KSA916





MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





TO-92 3 8.0x4.9 (LEADFORMED) CASE 135AM

ISSUE B

DATE 14 JAN 2021

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, GATE REMAINS AND TIE BAR PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
А	3.70	3.90	4.10	
A1	1.25	1.45	1.65	
b	0.35	0.50	0.60	
b2	0.62		0.78	
с	0.35	0.45	0.55	
D	7.80	8.00	8.20	
Е	4.70	4.90	5.10	
E2	3.70	3.90	4.10	
е	1.27 BSC			
e2	2.50 BSC			
F	2.45 REF			
L	13.00 REF			
L2	1.50		1.90	
L3	2.60		3.40	
L4	10.40 REF			

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